

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A silicon carbide product that is free from any sintering agent, comprising formed by either single-crystalline silicon carbide or chemical vapor deposited polycrystalline silicon carbide, and used in manufacturing a semiconductor device and/or a dummy wafer of the silicon carbide being cleaned, wherein the single-crystalline silicon carbide or chemical vapor deposited polycrystalline silicon carbide are free from sintering agent and have wherein the silicon carbide product has a surface with a concentration of metal impurities equal to or less than 1×10^{11} atoms/cm².

2. (Previously Presented) The silicon carbide product according to claim 1, wherein said metal impurities are at least one of iron or an iron compound, Ni, and Cu and wherein each of iron or iron compound, Ni and Cu has a concentration of less than 1×10^{10} atoms/cm².

3. (Cancelled).

4. (Currently Amended) A silicon carbide product cleaning method used for manufacturing a semiconductor device and/or a dummy wafer and comprising immersing single-crystalline silicon carbide or chemical vapor deposited polycrystalline silicon carbide free from any sintering agent in an [[acid]] acidic solution, wherein:

the step of immersing the single-crystalline silicon carbide or the chemical vapor deposited polycrystalline silicon carbide in the acidic solution is performed before manufacturing the semiconductor device and/or the dummy wafer and reduces surface iron or iron compound, Ni or Cu impurities of the single-crystalline silicon carbide or the chemical vapor deposited polycrystalline silicon carbide such that each of the iron or iron compound, Ni and Cu impurities has a concentration of less than 1×10^{10} atoms/cm² and

wherein:

the acidic solution is selected such that each of the iron or iron compound, Ni and Cu impurities is reduced by the acidic solution at a removal ratio (%) not smaller than 98%, wherein the removal ratio is represented by (100-(amount after cleaning/amount before cleaning)) x 100.

5. (Currently Amended) A method of manufacturing a silicon carbide product that is composed of single-crystalline silicon carbide or chemical vapor deposited polycrystalline silicon carbide and used for manufacturing a semiconductor device and/or a dummy wafer, comprising:

forming the single-crystalline silicon carbide or the chemical vapor deposited polycrystalline silicon carbide; and

cleaning the single-crystalline silicon carbide or the chemical vapor deposited polycrystalline silicon carbide only by an acidic solution to reduce surface iron or iron compound, Ni or Cu impurities such that each of the iron or iron compound, Ni and Cu impurities has a concentration of less than 1×10^{10} atoms/cm²;

wherein:

the acidic solution is selected such that each of the iron or iron compound, Ni or Cu impurities is reduced by the acidic solution at a removal ratio (%) which is not smaller than 98%, wherein the removal ratio is represented by (100-(amount after cleaning/amount before cleaning)) x 100.

6. (Currently Amended) The method according to claim 5, wherein said acid is acidic solution comprises hydrofluoric acid or hydrochloric acid.

7. (Original) The method according to claim 6, wherein said hydrofluoric acid has a concentration exceeding 45%.

8. (Original) The method according to claim 7, wherein said hydrofluoric acid has a concentration of about 50%.

9. (Original) The method according to claim 6, wherein said hydrochloric acid has a concentration of 35% or more.

10. (Original) The method according to claim 9, wherein said hydrochloric acid has a concentration of about 36%.

11. (Currently Amended) The method according to claim 5, wherein said ~~acid is acidic~~ solution comprises a liquid containing sulfuric acid and a hydrogen peroxide solution.

12. (Original) The method according to claim 11, wherein said liquid containing said sulfuric acid and said hydrogen peroxide solution has a pH of 4 or less.

13. (Original) The method according to claim 12, wherein said sulfuric acid and said hydrogen peroxide solution respectively have concentrations of about 97% and about 30% and are mixed in a volume ratio of about 4:1.

14. (Previously Presented) A silicon carbide product free from sintering agent and manufactured by the method according to claim 5, said silicon carbide product being a semiconductor device, a semiconductor device manufacturing member, or a structure.

15-16. (Cancelled).